Oral presentation | 15. Crystal Engineering | 15.4 III-V-group nitride crystals

[18p-C5-1~19]15.4 III-V-group nitride crystals

Thu. Sep 18, 2014 1:30 PM - 7:15 PM C5 (Open Hall)

△ : Young Scientist Oral Presentation Award Applied

▲ : English Presentation

▼ : Both Award Applied and English Presentation

1:30 PM - 2:00 PM

[18p-C5-1][JSAP Paper Award Speech] (30min.) Performance and Reliability of Deep-Ultraviolet Light-Emitting Diodes Fabricated on AlN Substrates Prepared by Hydride Vapor Phase Epitaxy

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